99.99 167.53 167.53 167.53	ાણાક	SSIFICATION
9/8/8/8/8/8/8/8/8/8/8/8/8/8/8/8/8/8/8/8	(Class	ISSUEIGUA

APPLICANTS



U.S. UTILITY Patent Application
O.I.P.E. PATENT DATE

			, ,		
	CONT/DDIOD	CLASS	SUBCLASS	ART UNIT	EXAMINER
APPLICATION NO. 09/881675	CONT/PRIOR F	257	335	2811	T. TRAN

Youichi Ishimura Yoshifumi Tomomatsu

Field-effect semiconductor device

			ISSUING (CLASSIFICA	TION		
ORIGIN	AL.	$T^{-}T$	CROSS REFERENCE(S)				
CLASS	SUBC	LASS	CLASS	SUBCLAS	S (ONE SUBCLASS PER BLOCK)		
CEROO	1						
INTERNATIONA	LOLACCIE	CATION					
INTERNATIONA	L CLASSIF	CATION					
							
				 -			
				 			
					Sile Isside Sile Issket		
				ll <u> </u>	Continued on Issue Slip Inside File Jacket		

TERMINAL	DRAWINGS			CLAIMS ALLOWED		
DISCLAIMER	Sheets Drwg.	Figs. Drwg.	Print Fig.	Total Claims	Print Claim for Q.G	
		L		NOTICE OF ALI	OWANCE MAILED	
The term of this patent subsequent to (date) has been disclaimed.	(Assistant Examiner)		(Date)	**		
The term of this patent shall not extend beyond the expiration date				ISSUE FEE		
of U.S Patent. No		•		Amount Due	Date Paid	
	(Primary Examiner) (Date)				<u> </u>	
	(Finally Common)		ISSUE BA	TCH NUMBER		
The terminalmonths of		•	• '!			
this patent have been disclaimed.	(Legal Instru	ments Exeminer)	(Date)			
The terminalmonths of this patent have been disclaimed. WARNING: The information disclosed herein may be repossession outside the U.S. Patent & Trade	(Legal Instru	d displaces may be	prohibited by the	United States Code Title ctors only.	35, Sections 122, 181	

BEST AVAILABLE CCT.